IXYS

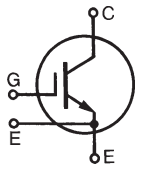
Preliminary Technical Information

GenX3™ 600V IGBT

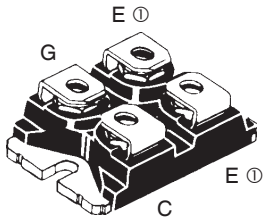
IXGN72N60A3

V_{CES} = 600V
I_{C110} = 68A
$V_{CE(sat)} \leq$ 1.35V

Ultra Low Vsat PT IGBT for
up to 5kHz switching



SOT-227B, miniBLOC
E153432



G = Gate, C = Collector, E = Emitter

①Either emitter terminal can be used as Main or Kelvin Emitter

Symbol	Test Conditions		Maximum Ratings	
V_{CES}	T_J = 25°C to 150°C		600	V
V_{CGR}	T_J = 25°C to 150°C, R_{GE} = 1MΩ		600	V
V_{GES}	Continuous		±20	V
V_{GEM}	Transient		±30	V
I_{C25}	T_C = 25°C (Chip capability)		160	A
I_{C110}	T_C = 110°C		68	A
I_{LRMS}	Terminal Current Limit		100	A
I_{CM}	T_C = 25°C, 1ms		400	A
SSOA	V_{GE} = 15V, T_{VJ} = 125°C, R_G = 3Ω		I_{CM} = 150	A
(RBSOA)	Clamped inductive load		@ 0.8 • V_{CES}	
P_C	T_C = 25°C		360	W
T_J			-55 ... +150	°C
T_{JM}			150	°C
T_{stg}			-55 ... +150	°C
V_{ISOL}	50/60Hz	t = 1min	2500	V~
	$I_{ISOL} \leq$ 1mA	t = 1s	3000	V~
M_d	Mounting torque		1.5/13	Nm/lb.in.
	Terminal connection torque (M4)		1.3/11.5	Nm/lb.in.
Weight			30	g

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)		Characteristic Values Min.	Typ.	Max.	
BV_{CES}	I_C = 250μA, V_{GE} = 0V		600			V
$V_{GE(th)}$	I_C = 250μA, V_{CE} = V_{GE}		3.0		5.0	V
I_{CES}	V_{CE} = V_{CES}				75	μA
	V_{GE} = 0V	T_J = 125°C			750	μA
I_{GES}	V_{CE} = 0V, V_{GE} = ±20V				±100	nA
$V_{CE(sat)}$	I_C = 60A, V_{GE} = 15V, Note 1				1.35	V

Features

- Optimized for low conduction losses
- Isolation voltage 3000 V~
- Square RBSOA
- International standard package

Advantages

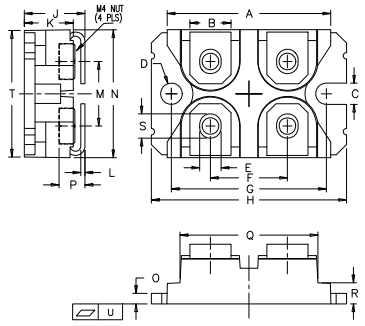
- High power density
- Low gate drive requirement

Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- Inrush Current Protection Circuits

Symbol	Test Conditions (T_J = 25°C, unless otherwise specified)	Characteristic Values Min.	Typ.	Max.	
g_{fs}	I_C = 60A, V_{CE} = 10V, Note 1	48	76		S
C_{ies}	V_{CE} = 25V, V_{GE} = 0V, f = 1MHz		6600		pF
C_{oes}			360		pF
C_{res}			80		pF
$Q_{g(on)}$	I_C = 60A, V_{GE} = 15V, V_{CE} = 0.5 • V_{CES}		230		nC
Q_{ge}			40		nC
Q_{gc}			78		nC
$t_{d(on)}$	**Inductive load, T_J = 25°C** I_C = 50A, V_{GE} = 15V V_{CE} = 480V, R_G = 3Ω		31		ns
t_{ri}			34		ns
E_{on}			1.38		mJ
$t_{d(off)}$			320		ns
t_{fi}			250		ns
E_{off}			3.5		mJ
$t_{d(on)}$	**Inductive load, T_J = 125°C** I_C = 50A, V_{GE} = 15V V_{CE} = 480V, R_G = 3Ω		29		ns
t_{ri}			32		ns
E_{on}			2.6		mJ
$t_{d(off)}$			510		ns
t_{fi}			375		ns
E_{off}			6.5		mJ
R_{thJC}				0.35	°C/W
R_{thCK}			0.05		°C/W

SOT-227B miniBLOC (IXGN)



SYM	INCHES MIN	INCHES MAX	MILLIMETERS MIN	MILLIMETERS MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

Note: 1. Pulse test, t ≤ 300µs; duty cycle, d ≤ 2%.

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from data gathered during objective characterizations of preliminary engineering lots; but also may yet contain some information supplied during a pre-production design evaluation. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

Fig. 1. Output Characteristics @ 25ºC

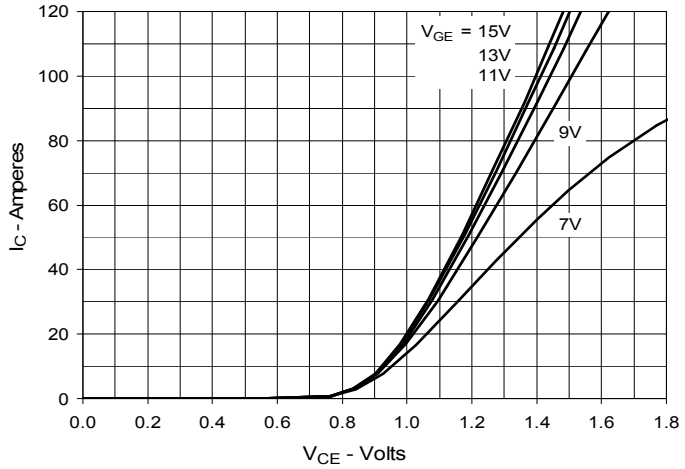


Fig. 2. Extended Output Characteristics @ 25ºC

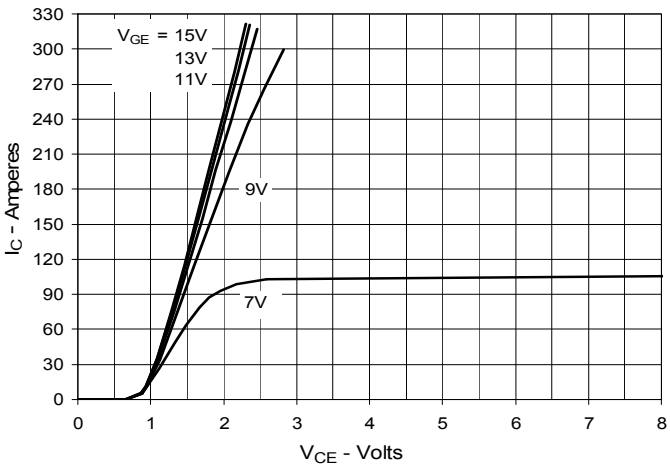


Fig. 3. Output Characteristics @ 125ºC

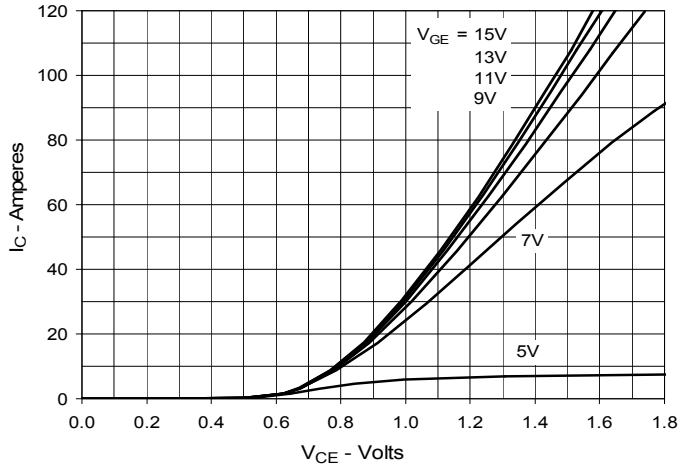


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

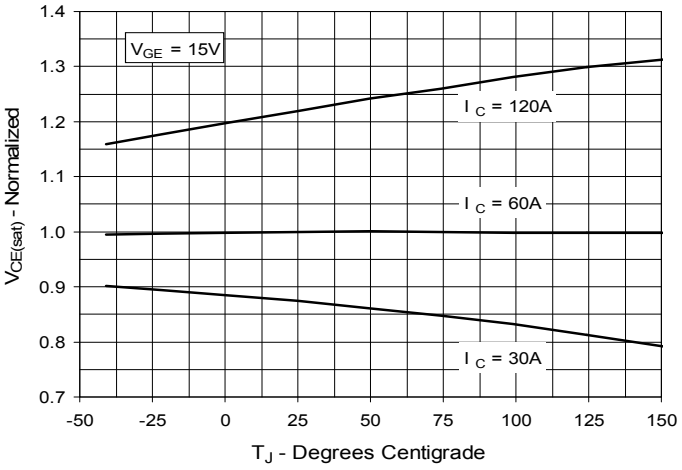


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

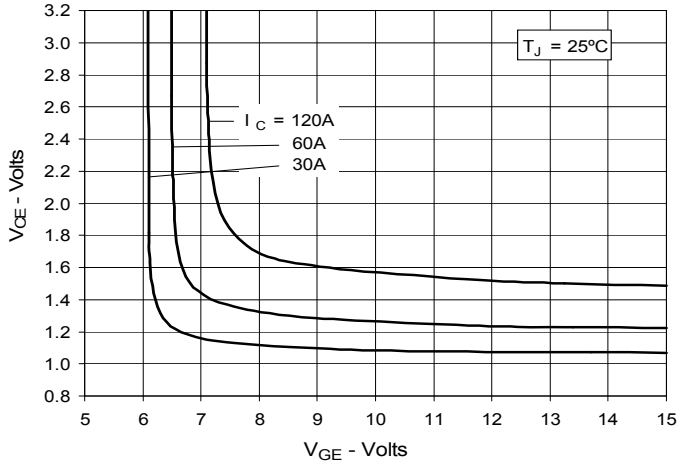


Fig. 6. Input Admittance

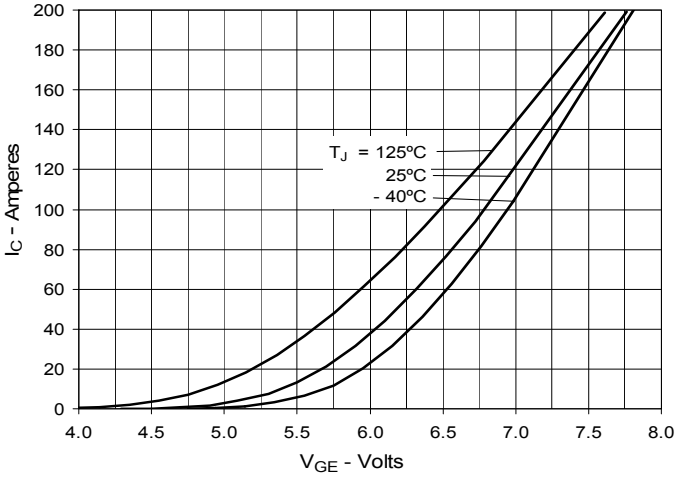


Fig. 7. Transconductance

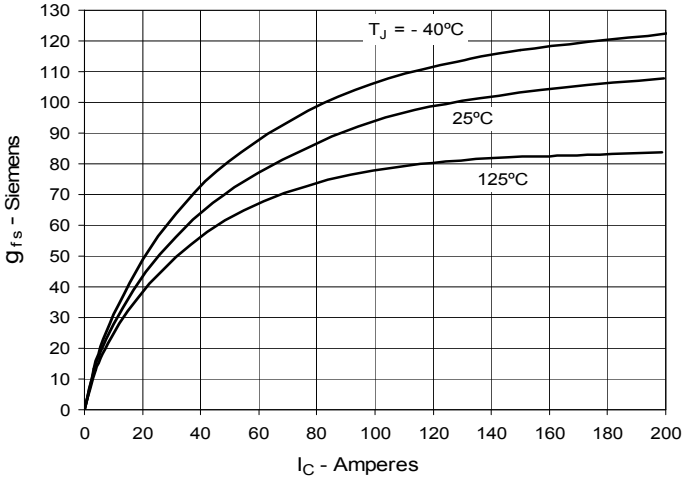


Fig. 8. Gate Charge

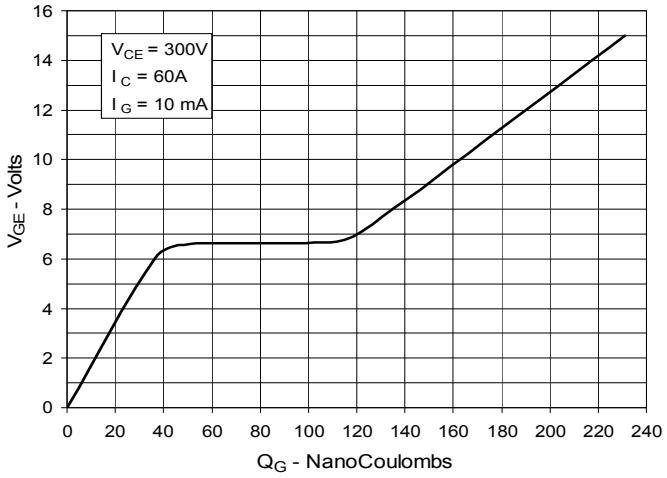


Fig. 9. Capacitance

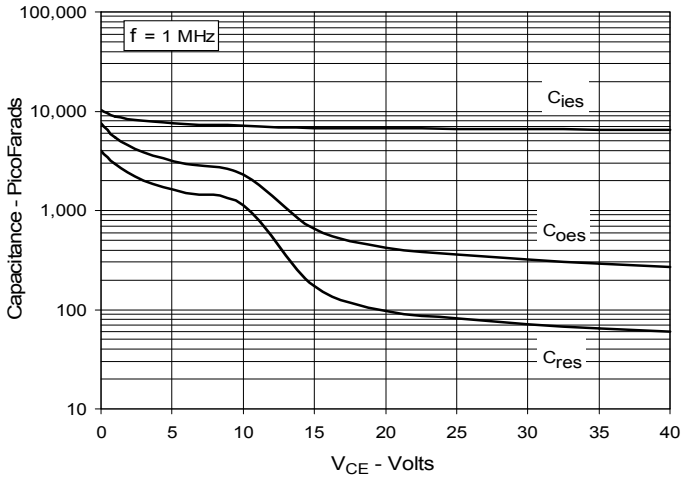


Fig. 10. Reverse-Bias Safe Operating Area

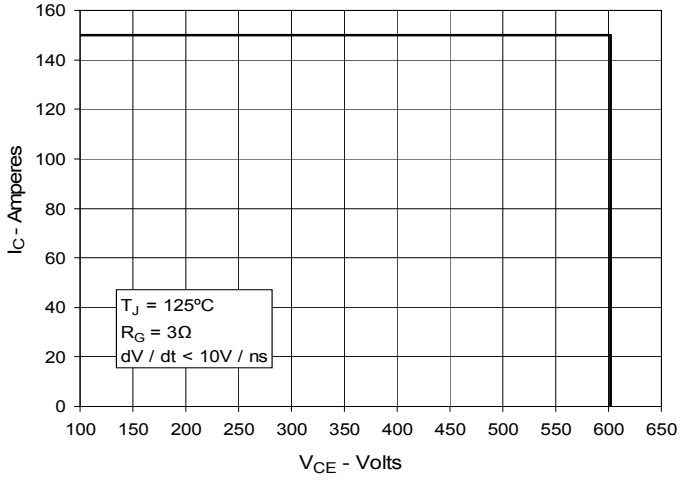


Fig. 11. Maximum Transient Thermal Impedance

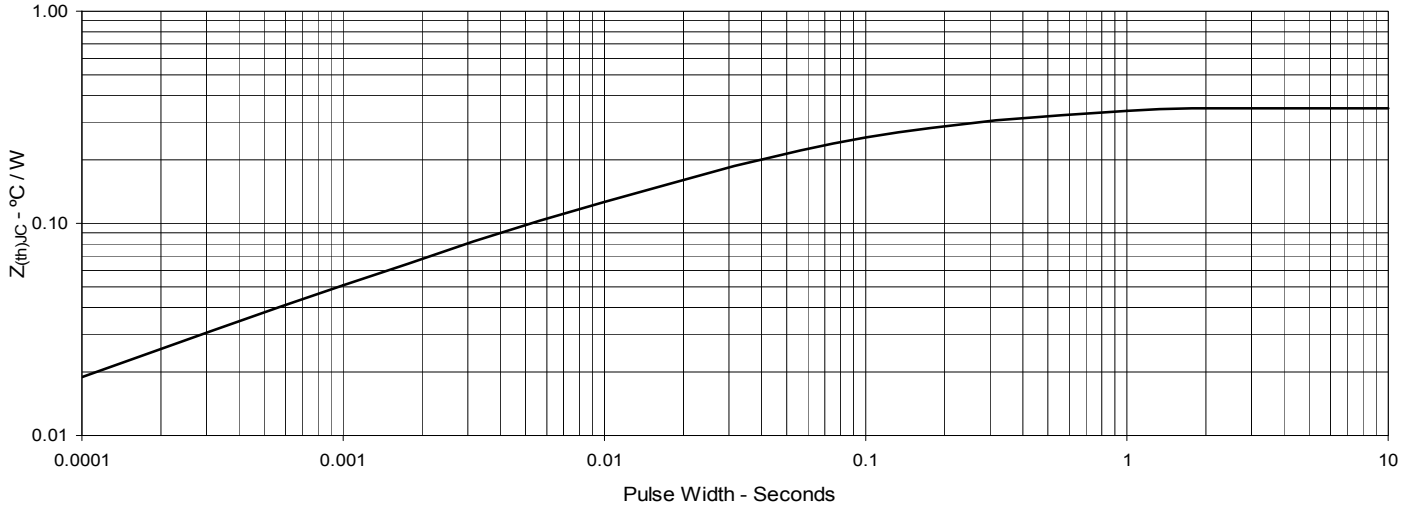


Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

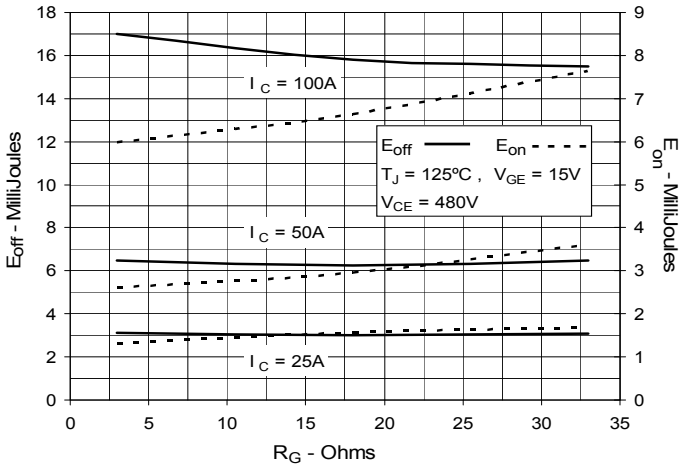


Fig. 13. Inductive Switching Energy Loss vs. Collector Current

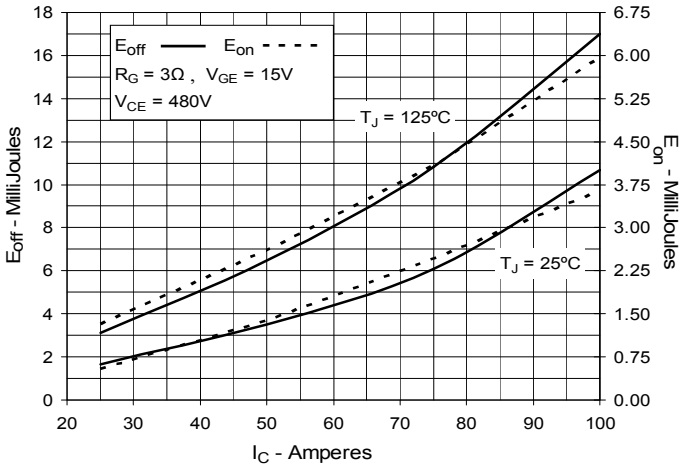


Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

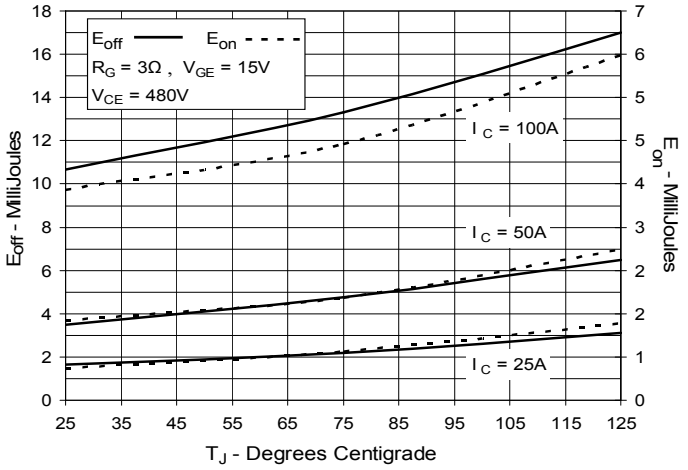


Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

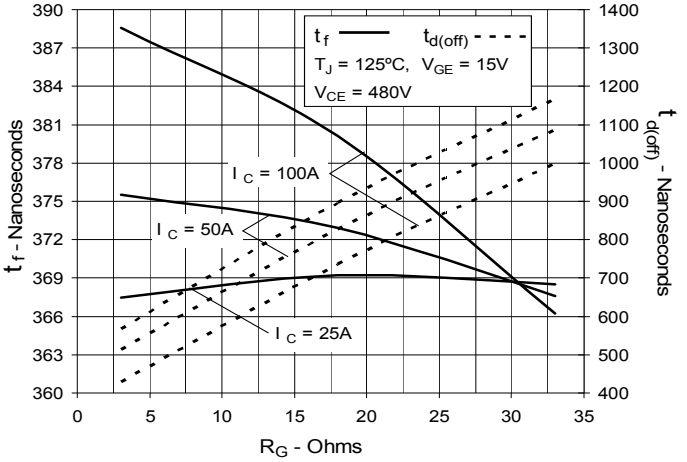


Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

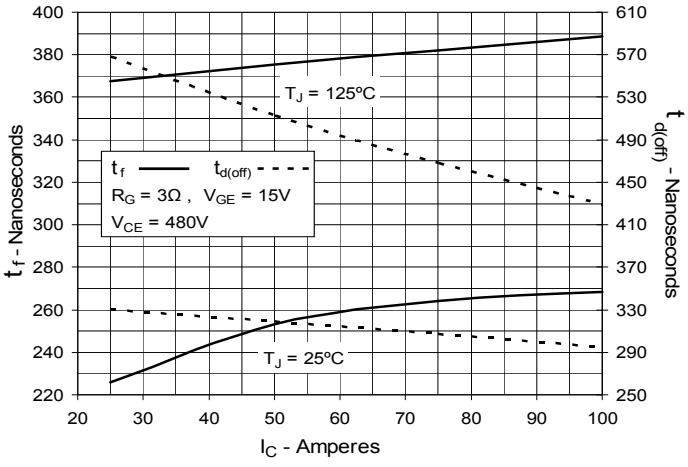


Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature

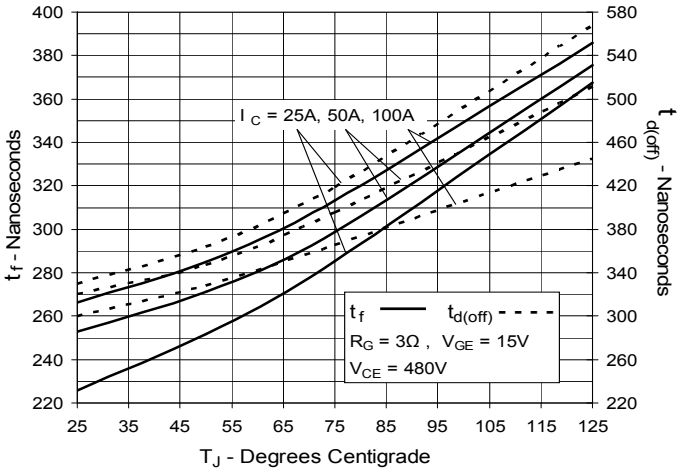


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

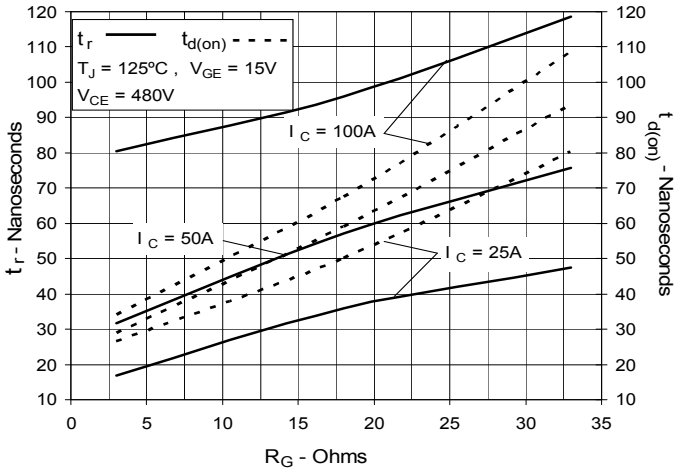


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

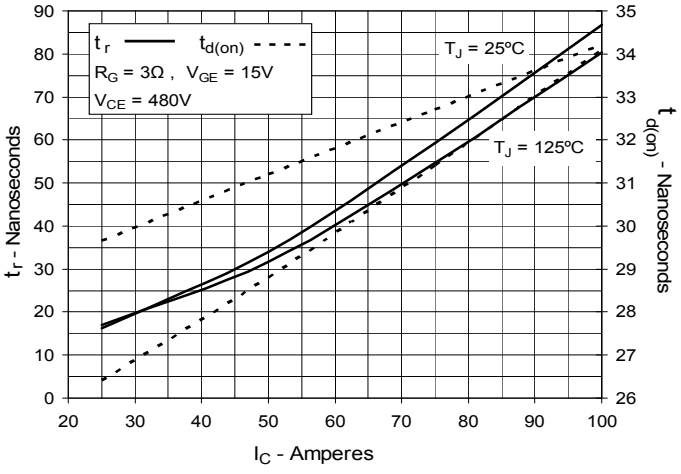


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature